




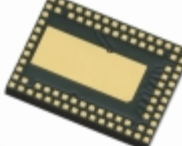
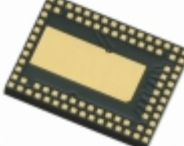





|   |   |
|---|---|
|  | <h2>SI1032X-T1-GE3</h2>   |
|   | <p><b>Hersteller-Teilenummer:</b> <a href="#">SI1032X-T1-GE3</a></p> <p><b>Hersteller / Marke:</b> <a href="#">Vishay / Siliconix</a></p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 20V 200MA SC89-3</p> <p><b>Datenblätter:</b>  <a href="#">SI1032X-T1-GE3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 42254 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation.<br/>See specs for product details.</p>            |   |

### Spezifikationen

|   |   |
|---|---|
| Teilenummer                                     | <a href="#">SI1032X-T1-GE3</a>                                      |
| Hersteller                                      | <a href="#">Vishay / Siliconix</a>                                  |
| Beschreibung                                    | MOSFET N-CH 20V 200MA SC89-3  |
| Kategorie                                       | <a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a> |
| Teilstatus                                      | 42254 pcs Stock   |
| Serie   | TrenchFET®  |
| Technologie                                     | MOSFET (Metal Oxide)  |
| Betriebstemperatur                              | -55°C ~ 150°C (TJ)  |
| Befestigungsart                                 | Surface Mount   |
| Verpackung / Gehäuse                            | SC-89, SOT-490  |
| Supplier Device-Gehäuse                         | SC-89-3   |
| Verlustleistung (max)                           | 300mW (Ta)  |
| Typ FET   | N-Channel   |
| FET-Merkmal                                     | -   |
| Drain-Source-Spannung (Vdss)                    | 20V   |
| Strom - Ununterbrochener Abfluss (Id) bei 25 °C | 200mA (Ta)  |
| Rds On (Max) @ Id, Vgs                          | 5 Ohm @ 200mA, 4.5V   |
| VGS (th) (Max) @ Id                             | 1.2V @ 250µA  |
| Gate Charge (Qg) (Max) @ Vgs                    | 0.75nC @ 4.5V   |
| Eingabekapazität (Ciss) (Max) @ Vds             | -   |
| Antriebsspannung (Max Rds On, Min Rds On)       | 1.5V, 4.5V  |
| Vgs (Max)                                       | ±6V   |
| Verpackung                                      | Tape & Reel (TR)  |



















































SI1032X-T1-GE3 ist neu im Original, Suche SI1032X-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1032X-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI1032X-T1-GE3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

|  |  |  |   |
|--|--|--|---|
|  <p><b>SI1032X-T1-GE3</b><br/>Electro-Films (EFI) / Vishay<br/>MOSFET N-CH 20V 200MA<br/>SC89-3</p> |  <p><b>SI1033-B-GM3</b><br/>Energy Micro (Silicon Labs)<br/>IC RF TXRX+MCU ISM&lt;1GHZ<br/>85-VFLGA</p> |  <p><b>SI1033-B-GM3R</b><br/>Energy Micro (Silicon Labs)<br/>IC RF TXRX+MCU ISM&lt;1GHZ<br/>85-VFLGA</p> |  <p><b>SI1032X-T1</b><br/>SILICON<br/>SI1032X-T1 SILICON</p>                             |
|  <p><b>SI1032X</b><br/>VISHAY<br/>SI1032X VISHAY</p>  |  <p><b>SI1033X-T1</b><br/>SILICON<br/>SI1033X-T1 SILICON</p>  |  <p><b>SI1032X-T1-E3</b><br/>Electro-Films (EFI) / Vishay<br/>MOSFET N-CH 20V 200MA<br/>SC89-3</p>       |  <p><b>SI1032X-T1-E3</b><br/>Vishay / Siliconix<br/>MOSFET N-CH 20V 200MA<br/>SC89-3</p> |

### heiße Teile

Mehr

|  |  |  |  |   |
|--|--|--|--|---|
|  SI1026X-T1-GE3 |  SI1026X-T1-GE3 |  SI1028X-T1-GE3 |  SI1028X-T1-GE3  |  SI1029X-T1-GE3  |
|  SI1029X-T1-GE3 |  SI1031R-T1     |  SI1031R-T1-E3  |  SI1031R-T1-E3   |  SI1031R-T1-GE3  |
|  SI1031R-T1-GE3 |  SI1031X-T1     |  SI1031X-T1-E3  |  SI1031X-T1-E3   |  SI1031X-T1-GE3  |
|  SI1031X-T1-GE3 |  SI1032R-T1     |  SI1032R-T1-E3  |  SI1032R-T1-E3   |  SI1032R-T1-GE3  |
|  SI1032R-T1-GE3 |  SI1032X-T1     |  SI1032X-T1-E3  |  SI1032X-T1-E3   |  SI1032X-T1-GE3  |
|  SI1033X-T1     |  SI1033X-T1-E3  |  SI1033X-T1-E3  |  SI1034CX-T1-GE3 |  SI1034CX-T1-GE3 |
|  SI1034X-T1     |  SI1034X-T1-E3  |  SI1034X-T1-E3  |  SI1034X-T1-GE3  |  SI1034X-T1-GE3  |
|  SI1035X-T1     |  SI1035X-T1-E3  |  SI1035X-T1-E3  |  SI1035X-T1-GE3  |  SI1035X-T1-GE3  |
|  SI1039X-T1-E3  |  SI1039X-T1-E3  |  SI1040X-T1-E3  |  SI1040X-T1-E3   |  SI1040X-T1-GE3  |
|  SI1040X-T1-GE3 |  SI1041ADY      |  SI1041DY-T1    |  SI1041DY-T1-E3  |  SI1045AB        |

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